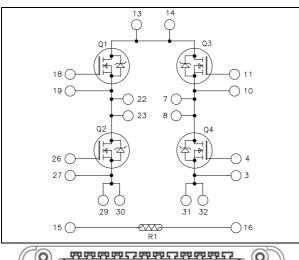


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### Full - Bridge MOSFET Power Module





All multiple inputs and outputs must be shorted together Example: 13/14 ; 29/30 ; 22/23 ...

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### $V_{DSS} = 500V$

 $R_{DSon} = 140 m\Omega \text{ typ}$  (a)  $Tj = 25^{\circ}C$ 

 $I_D = 26A$  (a)  $T_c = 25^{\circ}C$ 

### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

### Features

- Power MOS 7<sup>®</sup> FREDFETs
  - Low R<sub>DSon</sub>
  - Low input and Miller capacitance
  - Low gate charge
  - Fast intrinsic reverse diode
  - Avalanche energy rated
  - Very rugged
  - Kelvin source for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

### All ratings (a) $T_i = 25^{\circ}C$ unless otherwise specified

### Absolute maximum ratings (Per MOSFET)

Symbol	Parameter		Max ratings	Unit
V <sub>DSS</sub>	Drain - Source Voltage		500	V
т	Continuous Proin Current	$T_c = 25^{\circ}C$	26	
$1_{\rm D}$	$I_D$ Continuous Drain Current $T_c$	$T_c = 80^{\circ}C$	18	А
I <sub>DM</sub>	Pulsed Drain current		105	
$V_{GS}$	Gate - Source Voltage		$\pm 30$	V
R <sub>DSon</sub>	Drain - Source ON Resistance		168	mΩ
PD	Power Dissipation $T_c = 25^{\circ}C$		208	W
I <sub>AR</sub>	Avalanche current (repetitive and non repetitive)		35	А
EAR	Repetitive Avalanche Energy		30	rn I
E <sub>AS</sub>	Single Pulse Avalanche Energy		1300	mJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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### Electrical Characteristics (Per MOSFET)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$			100	μΑ
R <sub>DS(on)</sub>	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 13A$		140	168	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1 \text{mA}$	3		5	V
I <sub>GSS</sub>	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

### Dynamic Characteristics (Per MOSFET)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C <sub>iss</sub>	Input Capacitance	$V_{GS} = 0V$		3259		
Coss	Output Capacitance	$V_{DS} = 25V$		709		pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1 MHz		51		
Qg	Total gate Charge	$V_{GS} = 10V$		72		
$Q_{gs}$	Gate – Source Charge	$V_{Bus} = 250V$		20		nC
$Q_{gd}$	Gate – Drain Charge	$I_D = 26A$		36		1
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive switching @ 125°C		10		
Tr	Rise Time	$V_{GS} = 15V$		17		
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 333V$ $I_D = 26A$		50		ns
$T_{\mathrm{f}}$	Fall Time	$R_G = 5\Omega$		41		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		326		T
$E_{\text{off}}$	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 26A, R_G = 5\Omega$		250		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 26A, R_G = 5\Omega$		548		т
$E_{\text{off}}$	Turn-off Switching Energy			288		μJ
$R_{thJC}$	Junction to Case Thermal Resistance	· · · · · · · · · · · · · · · · · · ·			0.6	°C/W

### Source - Drain diode ratings and characteristics (Per MOSFET)

Symbol	Characteristic	Test Conditions	,	Min	Тур	Max	Unit
Is	Continuous Source current		$Tc = 25^{\circ}C$		26		А
IS	(Body diode)		$Tc = 80^{\circ}C$		18		А
V <sub>SD</sub>	Diode Forward Voltage	$V_{GS} = 0V, I_S = -26A$	L			1.3	V
dv/dt	Peak Diode Recovery <b>1</b>					15	V/ns
t <sub>rr</sub>		$I_{S} = -26A$ $V_{R} = 333V$	$T_j = 25^{\circ}C$			250	
	Reverse Recovery Time		$T_j = 125^{\circ}C$			525	ns
Q <sub>rr</sub>	Reverse Recovery Charge	$di_{\rm S}/dt = 100 {\rm A}/\mu{\rm s}$	$T_j = 25^{\circ}C$		1.6		μC
	Reverse Recovery Charge		$T_j = 125^{\circ}C$		6		μΟ

• dv/dt numbers reflect the limitations of the circuit rather than the device itself. I<sub>S</sub>  $\leq$  - 26A di/dt  $\leq$  700A/ $\mu$ s V<sub>R</sub>  $\leq$  V<sub>DSS</sub> T<sub>j</sub>  $\leq$  150°C



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### Thermal and package characteristics

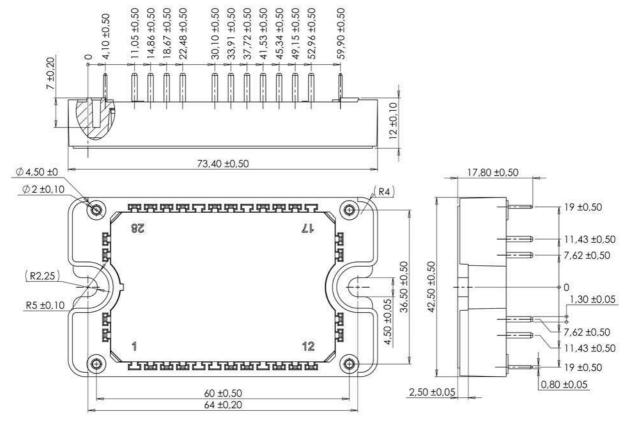
Symbol	Characteristic			Min	Max	Unit
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
TJ	Operating junction temperature range			-40	150	
T <sub>JOP</sub>	Recommended junction temperature under switching conditions			-40	T <sub>J</sub> max - 25	°C
T <sub>STG</sub>	Storage Temperature Range			-40	125	C
T <sub>C</sub>	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C	nce @ 25°C		50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B <sub>25/85</sub>	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		$T_C=100^{\circ}C$		4		%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

### Package outline (dimensions in mm)



See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

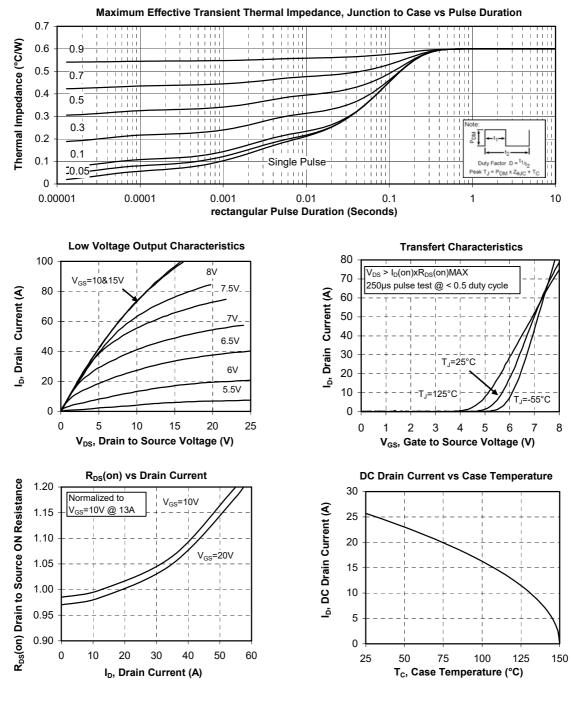
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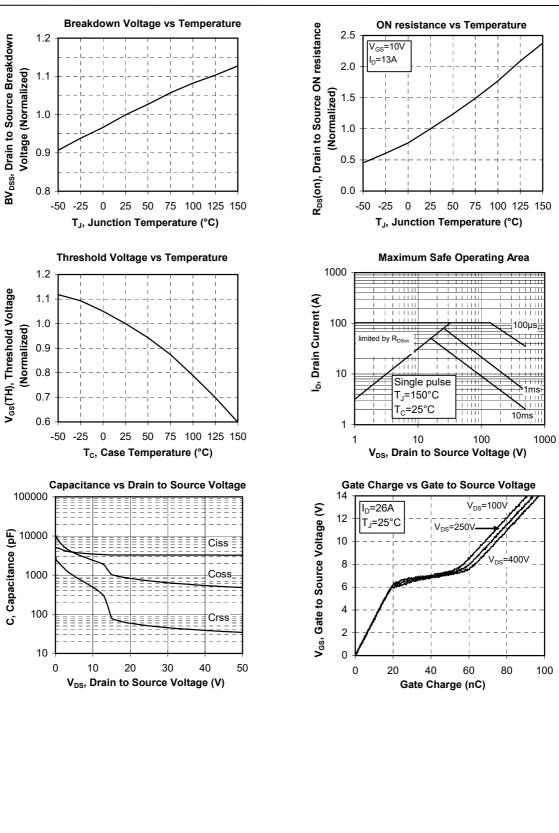
### **Typical Performance Curve**





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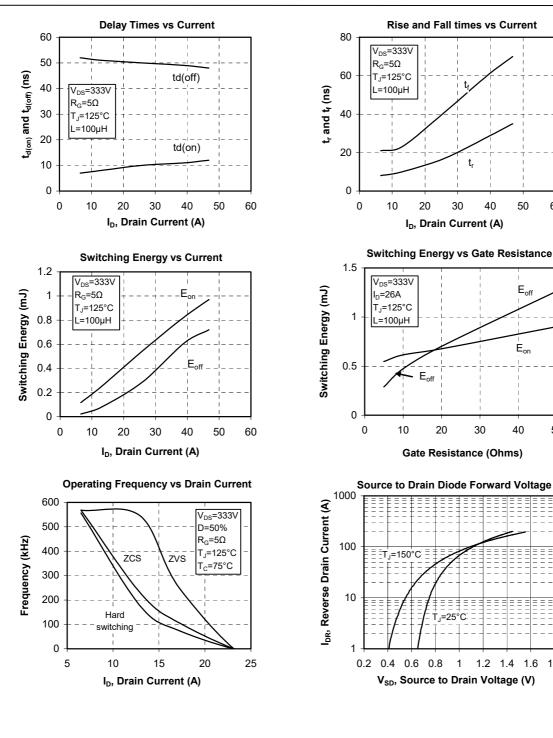
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